OPTICAL FIBER Materials Manufacturing-II

Fiber Structure



- An optical fiber is a long cylindrical dielectric waveguide, usually of circular cross-section, transparent to light over the operating wavelength.
- A single solid dielectric of two concentric layers. The inner layer known as Core is of radius 'a' and refractive index 'n₁'. The outer layer called Cladding has refractive index 'n₂'.

$n_2 < n_1 \rightarrow$ condition necessary for TIR

Light Propagation through Optical Fiber



Must meet the conditions for Total Internal Reflection (TIR)

Step Index / Graded Index



DESIGNER'S PARAMETERS

Numerical Aperture (NA) : $NA = \sin\theta_a = [(n_1)^2 - (n_2)^2]^{1/2}$

0.12-0.15 for SMF, 0.15-0.25 for MMF

Relative Refractive Index Difference (Δ):

 $\Delta = (n_1 - n_2)/n$; n- the average refractive index < 0.4% for SMF, >1% for MMF

Normalized Frequency or V-Number: $V = [(2\pi a)/\lambda] NA$ $V \le 2.405$ for SMF; ≥ 10 for MMF

Schematic of Vapour-Phase Deposition Techniques



Step-II-Fiber Drawing



- Rod in tube process
- Useful only for Step Index fibers with large core and cladding diameters.
- Bubbles & particulates at interfaces
- 5-10 dB/km loss

Optical Fiber from a Preform.

Outside Vapour-Phase Oxidation (OVPO) Process

- Uses Flame hydrolysis for 'Soot' Formation



- High OH impurity content
- Cracks during mandral removal

OVPO Process: (a) Soot deposition, (b) Preform Sintering (c) Fiber Drawing

VAD Process



The VAD Process

- End-on deposition
- Typical OH content between 50-200 PPM
- Reduced by applying chlorine as drying agent
- Typical Temp. 1500 ^oC
- Losses as low as 2 dB/km

Difficulties:

- Cracks while removing mandral
- Depression in RL profile near centre due to collapsed hole.

MCVD Techniques

- Modified Chemical Vapor Deposition (MCVD)
 - An inside vapour phase oxidation (IVPO) method

Fiber

vaporized raw materials are deposited into a pre-made silica tube



(C)

Preform rod

- Deposition within an enclosed reactor-very clean environment
- Fiber formation 1400-1600 °C, drawing at 2000 - 2200 °C
- Reduced OH impurity
- Minimum losses of only 0.2 dB/km at 1550 nm

PCVD Technique

- Plasma Activated Chemical Vapour Deposition
 - A variation on the MCVD technique to use plasma to supply energy for the vapour-phase oxidation of halides.
 - Film deposition at around 1000 ^oC



Provide controlled and high uniformity of layers

